

Thyristors type T75 are of modern design with pressure contacts, high alumina ceramic insulator and cold-welding encapsulation. Designed for use in power electronic circuits and equipment under normal operating conditions.

**KEY PARAMETERS**

$U_{DRM}, U_{RRM}$	<b>up to 2000 V</b>
$I_{T(AV)}$	<b>700 A</b>
$I_{TSM}$	<b>8800 A</b>
$du/dt^*$	<b>1000 V/<math>\mu</math>s</b>
$di/dt$	<b>150 A/<math>\mu</math>s</b>

\* maximum (non standard) value

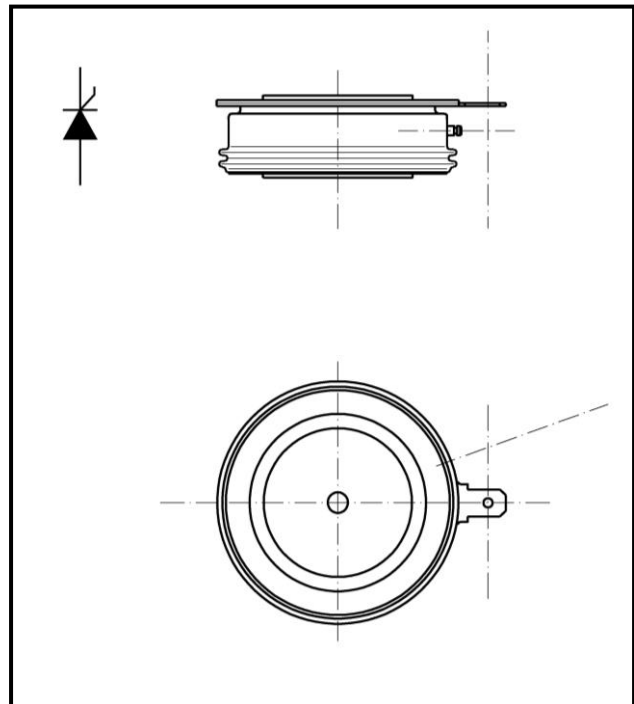
**FEATURES**

- all diffused design
- high current capabilities
- high surge current capabilities
- high rates voltages
- high  $du/dt$
- low gate current
- dynamic gate
- low thermal impedance
- tested according to IEC standards
- compact size and small weight

**APPLICATION**

- High Power Drives
- DC Motor Control
- High Voltage Power Supplies

Designed for use in high power industrial and commercial electronic circuits and equipment where high currents are encountered and high reliability is essential.



**Outline type code: JEDEC TO-200AB**  
**(E-puk)**

See package details for further information

**ORDERING INFORMATION**

When ordering please refer to device code builder presented below.  
 Please use the complete part number when ordering, quote or in any future correspondence relating to your order.

**T75-700-□□**



This is standard device, with no dynamic parameters specified and standard accessory set.  
 Please refer to **Electrical Parameters** if specific dynamic demands have to be met.  
 Those information, as well as any other concerning non-standard accessories e.g. custom leads length or lead terminal connector type should be included in the order.

**ELECTRICAL PARAMETERS**

**Voltage ratings**

Voltage class	$U_{DRM}, U_{RRM}$	$U_{DSM}, U_{RSM}$	$I_{DRM}, I_{RRM}$
	V	V	mA
04	400	500	30
06	600	700	
08	800	900	
10	1000	1100	
12	1200	1300	
14	1400	1500	
16	1600	1700	
18	1800	1900	
20	2000	2100	

**du/dt group codes**

Group code	du/dt
	V/ $\mu$ s
0	no specified value
5	320
6	500
7	1000

**Electrical properties**

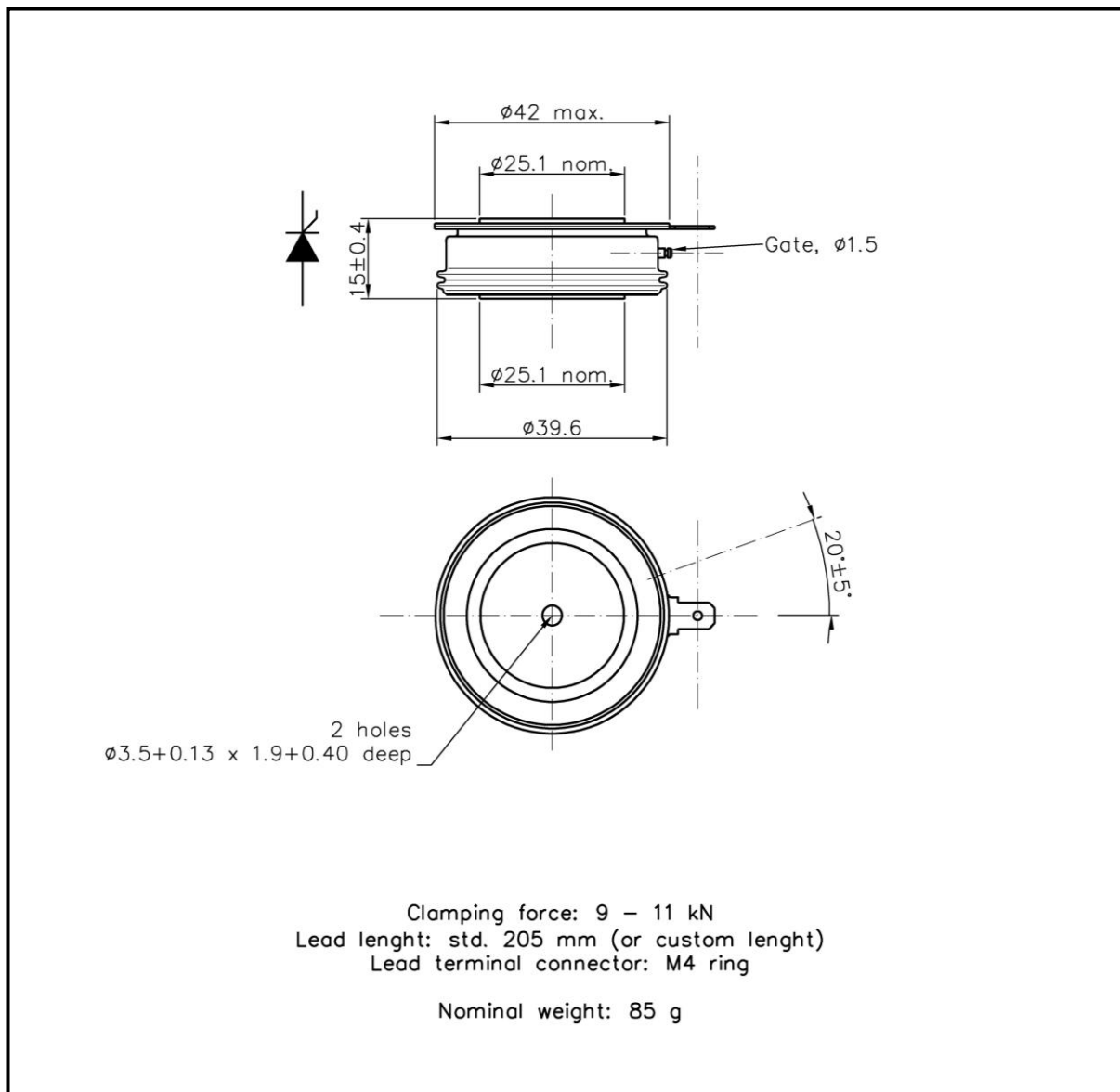
Parameter	Unit	Test conditions	Value
Average on-state current	$I_{T(AV)}$	A	700
Case temperature	$T_c$	°C	65
RMS on-state current	$I_{T(RMS)}$	A	1100
Surge on-state current	$I_{TSM}$	A	$T_j=125^\circ\text{C}$ , $U_R=0,8U_{RRM}$ , $t_p=10\text{ms}$
$I^2t$ – value	$I^2t$	$\text{kA}^2\text{s}$	386
On-state voltage max.	$U_{TM}$	V	$T_j=25^\circ\text{C}$ , $I_{TM}=1500\text{A}$
Threshold voltage	$U_{T(T0)}$	V	0,87
Slope resistance	$r_T$	$\text{m}\Omega$	0,60
Latching current	$I_l$	mA	$T_j=25^\circ\text{C}$ , $U_D=12\text{V}$
Holding current	$I_H$	mA	$T_j=25^\circ\text{C}$ , $U_D=12\text{V}$
Circuit commutated turn-off time (typical)	$t_q$ (typ)	$\mu\text{s}$	$T_j=125^\circ\text{C}$ , $I_{TM}=250\text{A}$ , $di_R/dt=25\text{A}/\mu\text{s}$ , $du/dt=20\text{V}/\mu\text{s}$ , $U_D=0,67U_{DRM}$ , $U_{RM}=100\text{V}$
Turn-On time (typical)	$t_{on}$	$\mu\text{s}$	$I_{TM}=100\text{A}$ , $U_{DM}=100\text{V}$
Rate of rise of on-state current-repetitive	$di/dt$	$\text{A}/\mu\text{s}$	$T_j=125^\circ\text{C}$ , $I_{TM}=3I_{T(AV)}$ , $U_D=0,67U_{DRM}$ , $f=50\text{Hz}$ , $I_{GM}=1\text{A}$ , $di_G/dt=1\text{A}/\mu\text{s}$
Critical rate of raise of off-state voltage	$du/dt$	$\text{V}/\mu\text{s}$	$T_j=125^\circ\text{C}$ , $U_D=0,67U_{DRM}$
Gate current to trigger	$I_{GT}$	mA	$T_j=25^\circ\text{C}$ , $U_D=12\text{V}$
Gate voltage to trigger	$U_{GT}$	V	$T_j=25^\circ\text{C}$ , $U_D=12\text{V}$

**Thermal properties**

Parameter	Unit	Test conditions	Value
Thermal resistance, junction to case	$R_{thJC}$	°C/W	two sided, DC
Thermal resistance, case to heatsink	$R_{thCS}$	°C/W	two sided
Operating junction temperature	$T_{jmin} \dots T_{jmax}$	°C	-40...+125
Storage temperature	$T_{stg}$	°C	-40...+125

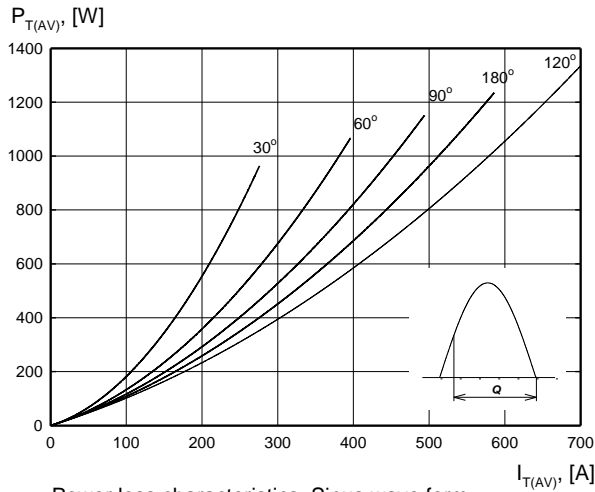
**Mechanical properties**

Parameter	Unit	Value
Clamping force	$F_M$	kN
Weight	m	g

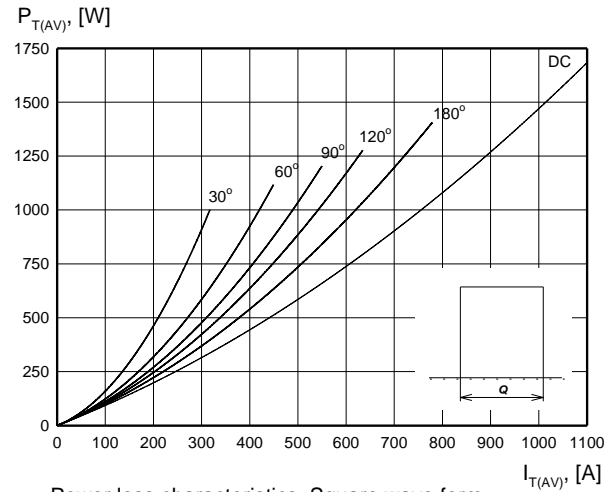
**Package details**

For further package information, please contact Sales & Marketing Department. All dimensions in mm, unless stated otherwise.  
Do not scale.

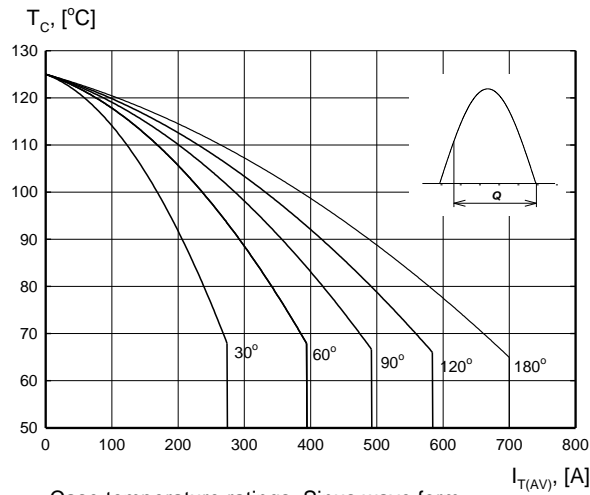
**CHARACTERISTICS**



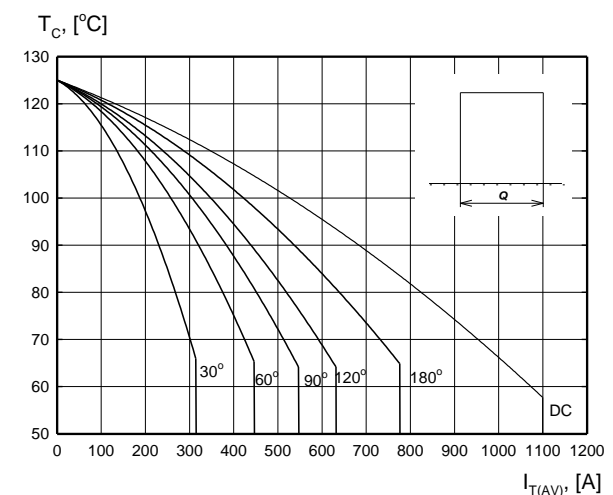
Power loss characteristics. Sinus wave form.



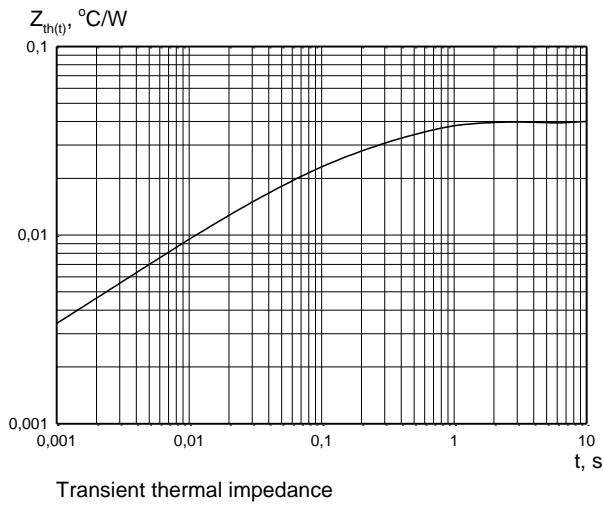
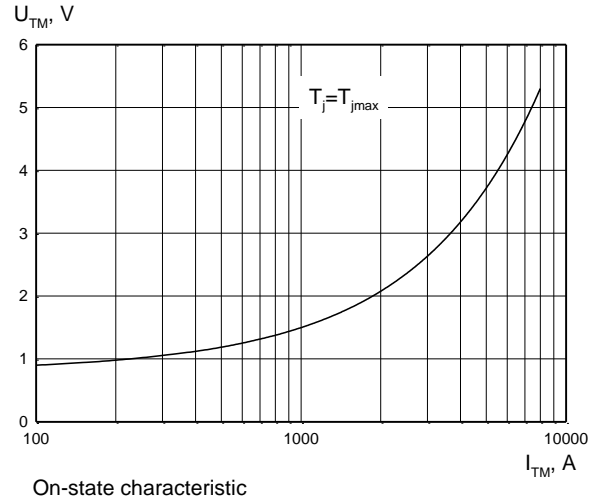
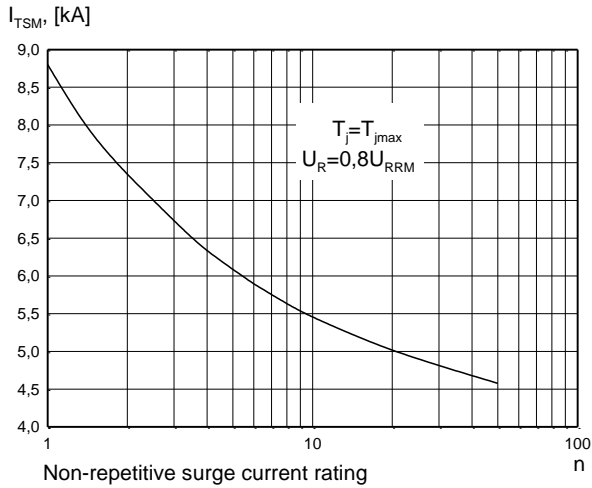
Power loss characteristics. Square wave form.



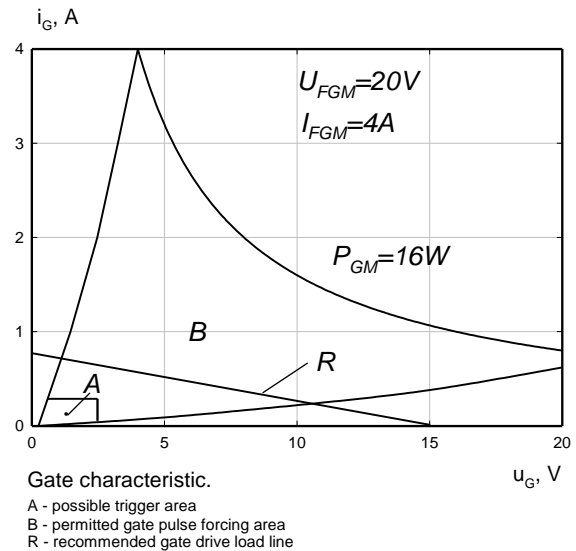
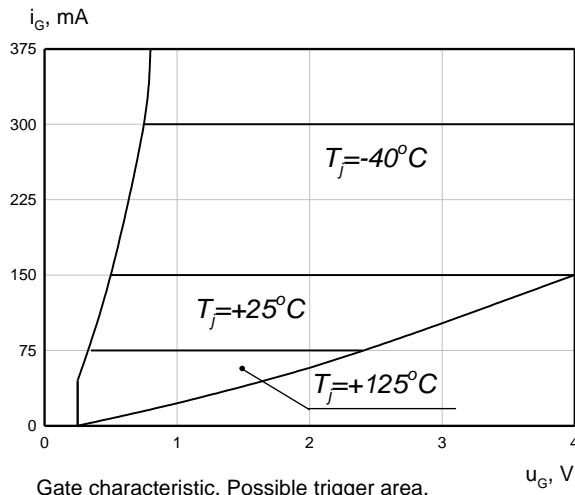
Case temperature ratings. Sinus wave form.



Case temperature ratings. Square wave form.



**Gate characteristics**



**HEATSINKS**

**KUBARA LAMINA SA** has its own proprietary range of extruded aluminium heatsinks designed to optimise the performance of our semiconductors with natural and forced air flow. High efficiency water cooled copper heatsinks are also available.

**DEVICE CLAMPS**

Disc devices require the correct clamping force to ensure their best operation.

**KUBARA LAMINA SA** offers a wide selection of clamps to suit all of our manufactured devices.

**POWER ASSEMBLY CAPABILITY**

**KUBARA LAMINA SA** provides a support for those customers requiring more than a basic semiconductor and offers precisely assembled Power Blocks according to factory or customer standards.